



Features

- 1.8V Supply Voltage
- Crystal/CMOS input: 50 MHz
- 8 Differential low power HCSL outputs with on-chip termination
- Individual output enable
- Reference CMOS output
- Programmable slew rate and output amplitude for each output
- Differential outputs blocked until PLL is locked
- Selectable 0%, -0.25% or -0.5% spread on differential outputs
- Strapping pins or SMBus for configuration
- 3.3V Tolerant SMBus interface support
- Very low jitter outputs
 - Differential cycle-to-cycle jitter < 50ps
 - Differential output-to-output skew < 60ps
 - PCIe Gen1~Gen6 compliant
 - CMOS REFOUT phase jitter < 250fs RMS
- Packaging (Pb-free & Green): 48-lead 6×6mm TQFN

Applications

- Cloud/High-performance Computing
- NVME Storage
- Networking
- PCIe switch

Description

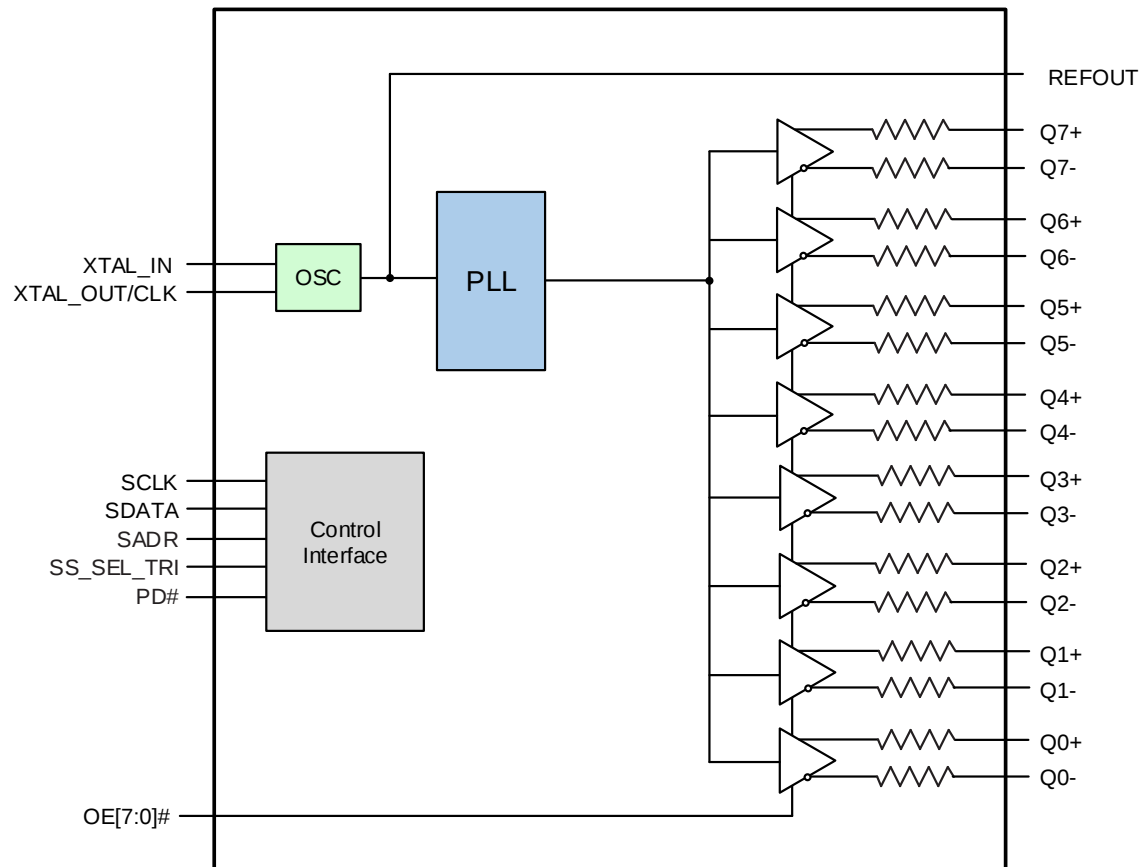
The RS2CG1818 is an 8-output very low power PCIe Gen1~Gen6 clock generator. It uses 50MHz crystal or CMOS reference as an input to generate the 100MHz low power differential HCSL outputs with on-chip terminations. The on-chip termination can save 32 external resistors and make layout easier. An additional buffered reference output is provided to serve as a low noise reference for other circuitry. It uses Raystar' proprietary PLL design to achieve very low jitter that meets PCIe Gen1~Gen6 requirements. It also provides various options such as different slew rate and amplitude through strapping pins or SMBUS so that users can configure the device easily to get the optimized performance for their individual boards. The device also supports selectable spread-spectrum options to reduce EMI for various applications.

Ordering Information

Part Number	Package	Description
RS2CG1818ZL	TQFN-48L	6 x 6 x 0.75 mm, 0.4mm Pitch

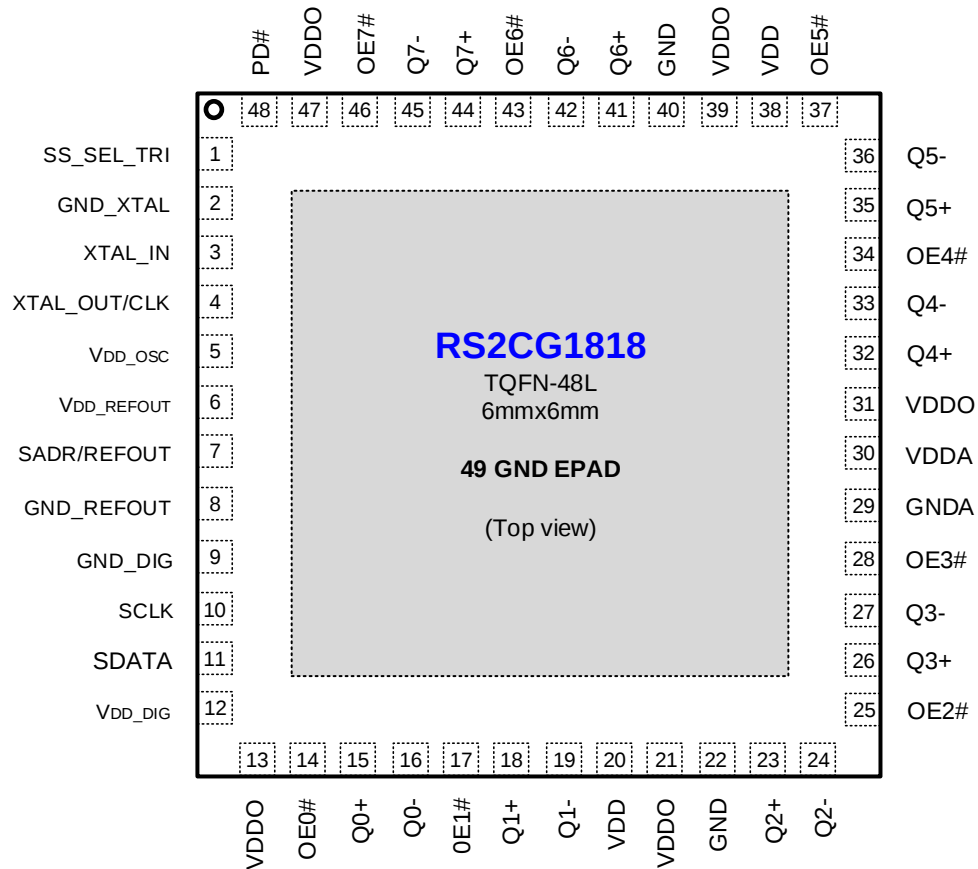


Block Diagram





Pin Configuration



Pin Description



Pin #	Pin Name	Type		Description
1	SS_SEL_TRI	Input	Tri-level	Latched select input to select spread spectrum amount at initial power up 1 = -0.5% spread, M = -0.25%, 0 = Spread Off
2	GND_XTAL	Power		Ground for oscillator circuit
3	XTAL_IN	Input		Crystal input
4	XTAL_OUT/CLK	Output		Crystal output or CMOS reference input
5	VDD_OSC	Power		Power supply for oscillator circuitry, nominal 1.8V
6	VDD_REFOUT	Power		Power supply for buffered CMOS output
7	SADR/REFOUT	Input/ Output	CMOS	Latch to select SMBus Address or 1.8V LVCMOS REFOUT. This pin has an internal pull-down
8	GND_REFOUT	Power		Ground for REFOUT
9	GND_DIG	Power		Ground for digital circuitry
10	SCLK	Input	CMOS	SMBUS clock input, 3.3V tolerant
11	SDATA	Input/ Output	CMOS	SMBUS Data line, 3.3V tolerant
12	VDD_DIG	Power		Power supply for digital circuitry, nominal 1.8V
13, 21, 31, 39, 47	VDDO	Power		Power supply for differential outputs
14	OE0#	Input	CMOS	Active low input for enabling Q0 pair. This pin has an internal pull-down. 1 = disable outputs, 0 = enable outputs
15	Q0+	Output	HCSL	Differential true clock output
16	Q0-	Output	HCSL	Differential complementary clock output
17	OE1#	Input	CMOS	Active low input for enabling Q1 pair. This pin has an internal pull-down. 1 = disable outputs, 0 = enable outputs
18	Q1+	Output	HCSL	Differential true clock output
19	Q1-	Output	HCSL	Differential complementary clock output
20, 38	VDD	Power		Power supply, nominal 1.8V
22, 40	GND	Power		Ground
23	Q2+	Output	HCSL	Differential true clock output
24	Q2-	Output	HCSL	Differential complementary clock output
25	OE2#	Input	CMOS	Active low input for enabling Q2 pair. This pin has an internal pull-down. 1 = disable outputs, 0 = enable outputs
26	Q3+	Output	HCSL	Differential true clock output
27	Q3-	Output	HCSL	Differential complementary clock output
28	OE3#	Input	CMOS	Active low input for enabling Q3 pair. This pin has an internal pull-down. 1 = disable outputs, 0 = enable outputs
29	GNDA	Power		Ground for analog circuitry
30	VDDA	Power		Power supply for analog circuitry
32	Q4+	Output	HCSL	Differential true clock output
33	Q4-	Output	HCSL	Differential complementary clock output



Pin #	Pin Name	Type		Description
34	OE4#	Input	CMOS	Active low input for enabling Q4 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
35	Q5+	Output	HCSL	Differential true clock output
36	Q5-	Output	HCSL	Differential complementary clock output
37	OE5#	Input	CMOS	Active low input for enabling Q5 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
41	Q6+	Output	HCSL	Differential true clock output
42	Q6-	Output	HCSL	Differential complementary clock output
43	OE6#	Input	CMOS	Active low input for enabling Q6 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
44	Q7+	Output	HCSL	Differential true clock output
45	Q7-	Output	HCSL	Differential complementary clock output
46	OE7#	Input	CMOS	Active low input for enabling Q7 pair. This pin has an internal pull- down. 1 =disable outputs, 0 = enable outputs
48	PD#	Input	CMOS	Input notifies device to sample latched inputs and start up on first high assertion. Low enters Power Down Mode, subsequent high assertions exit Power Down Mode. This pin has internal pull-up resistor.

SMBus Address Selection Table

	SADR	Address	+Read/Write Bit
State of SADR on first application of PD#	0	1101000	X
	1	1101010	X

Power Management Table

PD#	SMBus OE bit	OEn#	Qn+	Qn-
0	X	X	Low	Low
1	1	0	Running	Running
1	1	1	Low	Low
1	0	X	Low	Low

PD#	SMBus Byte3 [4]	REFOUT
0	X	X
1	0	Hiz
1	1	Running

Absolute Maximum Ratings



The absolute maximum ratings are stress ratings only. Stresses greater than those listed below can cause permanent damage to the device. Functional operation of the RS2CG2008 at absolute maximum ratings is not implied. Exposure to absolute maximum rating conditions may affect device reliability.

Parameter	Symbol	Conditions	MIN	TYP	MAX	Units	Notes
Supply Voltage	V _{DDX}				3.3	V	1
Input High Voltage	V _{IH}				V _{DD} +0.5	V	2
Input Low Voltage	V _{IL}		-0.5			V	
Storage Temperature	T _S		-65		150	°C	
Junction Temperature	T _J	Maximum operating junction temperature.			125	°C	
Input ESD Protection	ESD	Human Body Model.			2000	V	

1. Operation over these conditions is neither implied nor guaranteed.
2. Maximum V_{IH} is not to exceed maximum V_{DD}.

Recommend Operating Conditions

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V _{DD} , V _{DDO} V _{DDA} V _{DD_OSC} V _{DD_RE-FOUT} V _{DD_DIG}	Power Supply Voltage		1.71	1.8	1.89	V
I _{DDA}	Analog Power Supply Current	All outputs active @100MHz		12	15	mA
I _{DD}	Power Supply Current	All V _{DD} , except V _{DDA} and V _{DDO} , All outputs active @100MHz		5	7.5	mA
I _{DDO}	Power Supply Current for Outputs	All outputs active @100MHz		42	50	mA
I _{DDA_WL}	Analog Power Supply Wake-on-LAN ¹ Current	Q outputs off, REF output running		0.4	1	mA
I _{DD_WL}	Power Supply Wake-on-LAN ¹ Current	All V _{DD} , except V _{DDA} and V _{DDO} , Q outputs off, REF output running		0.5	1	mA
I _{DDO_WL}	Power Supply Wake-on-LAN ¹ Current for Outputs	Q outputs off, REF output running		0.04	0.1	mA
I _{DDA_PD}	Analog Power Supply Power Down ² Current	All outputs off		0.4	1	mA
I _{DD_PD}	Power Supply Power Down ² Current	All outputs off		0.6	1	mA
I _{DDO_PD}	Power Supply Current Power Down ² for Outputs	All outputs off		0.0005	0.1	mA
T _A	Ambient Temperature	Industrial grade	-40		125	°C

Note:

1. Wake-on-LAN mode: PD# = '0' Byte 3, bit 5 = '1'
2. Power down mode: PD# = '0' Byte 3, bit 5 = '0'



Input Electrical Characteristics

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
R _{pu}	Internal pull up resistance			120		KΩ
R _{dn}	Internal pull down resistance			120		KΩ
C _{XTAL}	Internal capacitance on X _{IN} and X _{OUT} pins			5		pF
LPIN	Pin inductance				7	nH

Crystal Characteristic

Parameters	Description	Min.	Typ	Max.	Units
OSCmode	Mode of Oscillation	Fundamental			
FREQ	Frequency		50		MHz
ESR ¹	Equivalent Series Resistance			50	Ω
C _{load}	Load Capacitance		8		pF
C _{shunt}	Shunt Capacitance			7	pF
	Drive Level			300	μW

Note:

1. ESR value is dependent upon frequency of oscillation

SMBus Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V _{DD} SMB	Nominal bus voltage		1.7		3.6	V
V _{IH} SMB	SMBus Input High Voltage	SMBus, V _{DD} SMB = 3.3V	2.1		3.6	V
		SMBus, V _{DD} SMB < 3.3V	0.65 V _{DD} SMB			
V _{IL} SMB	SMBus Input Low Voltage	SMBus, V _{DD} SMB = 3.3V			0.6	V
		SMBus, V _{DD} SMB < 3.3V			0.6	
I _{SMB} SINK	SMBus sink current	SMBus, at V _{OL} SMB	4			mA
V _{OL} SMB	SMBus Output Low Voltage	SMBus, at I _{SMB} SINK			0.4	V
f _{MAX} SMB	SMBus operating frequency	Maximum frequency			400	kHz
t _{RMSB}	SMBus rise time	(Max V _{IL} - 0.15) to (Min V _{IH} + 0.15)			1000	ns
t _{FMSB}	SMBus fall time	(Min V _{IH} + 0.15) to (Max V _{IL} - 0.15)			300	ns

Spread Spectrum Characteristic

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
f _{MOD}	SS Modulation Frequency	Triangular modulation	30	31.6	33	kHz



LVC MOS DC Electrical Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
V _{IH}	Input High Voltage	Single-ended inputs, except SMBus	0.75 V _{DD}		V _{DD} +0.3	V
V _{IM}	Input Mid Voltage	SS_SEL_TRI	0.4V _{DD}	0.5V _{DD}	0.55V _{DD}	V
V _{IL}	Input Low Voltage	Single-ended inputs, except SMBus	-0.3		0.25 V _{DD}	V
I _{IH}	Input High Current	Single-ended inputs, V _{IN} = V _{DD}			20	μA
I _{IL}	Input Low Current	Single-ended inputs, V _{IN} = 0V	-20			μA
I _{IH}	Input High Current	Single-ended inputs with pull up/pull down resistor, V _{IN} = V _{DD}			220	μA
I _{IL}	Input Low Current	Single-ended inputs with pull up/pull down resistor, V _{IN} = 0V	-220			μA
V _{OH}	Output High Voltage	REFOUT, except SMBus; I _{OH} = -2mA	V _{DD} -0.45			V
V _{OL}	Output Low Voltage	REFOUT, except SMBus; I _{OH} = 2mA			0.45	V
R _{OUT}	CMOS Output impedance			20		Ω
C _{IN}	Input Capacitance		1.5		5	pF

LVC MOS AC Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
f _{INPUT}	Input Frequency	XTAL_OUT/CLK		50		MHz
t _{RIN}	Input rise time	Single-ended inputs			5	ns
t _{FIN}	Input fall time	Single-ended inputs			5	ns
t _{STAB}	Clock stabilization	From Power-Up and after input clock stabilization or de-assertion of PD# to 1st clock		0.6	1.8	ms
t _{PDLAT}	PD# de-assertion	LVC MOS outputs enable after PD# de-assertion		20	300	μs
t _{PERIOD}	REFOUT clock period	REFOUT, assume input is at 50MHz		40		ns
f _{ACC}	REFOUT frequency accuracy ¹	REFOUT, long term accuracy to input		0		ppm
t _{SLEW}	REFOUT slew rate ¹	Byte 3 = 1F, 20% to 80% of V _{DDREF}	0.6	1	1.6	V/ns
		Byte 3 = 5F, 20% to 80% of V _{DDREF}	0.75	1.4	2.2	V/ns
		Byte 3 = 9F, 20% to 80% of V _{DDREF}	0.85	1.7	2.7	V/ns
		Byte 3 = DF, 20% to 80% of V _{DDREF}	1.0	1.8	2.9	V/ns
t _{DC}	REFOUT Duty Cycle ¹	V _T = V _{DD} /2 V, driven by a Xtal	45	50	55	%



LVC MOS AC Characteristics (Cont.)

Symbol	Parameters	Condition	Min.	Typ.	Max.	Units
t _{DCDIS}	REFOUT Duty Cycle Distortion	V _T = V _{DD} / 2 V, driven by an external source	0	2	4	%
t _{JITCC}	REFOUT cycle-cycle jitter	V _T = V _{DD} / 2 V, driven by a Xtal		19.1	250	ps
t _{JITPH}	REFOUT phase jitter	12kHz to 5MHz, RMS, driven by a Xtal		0.63	1.5	ps
t _{JITN}	Noise floor	1kHz offset, driven by a Xtal		-129.8	-105	dBc
		10kHz offset to Nyquist, driven by a Xtal		-143.6	-115	dBc

Note:

1. Guaranteed by design and characterization, not 100% tested in production

HCSL Output Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Typ.	Max.	Units
V _{OH}	Output Voltage High ¹	Statistical measurement on single-ended signal using oscilloscope math function	660	784	850	mV
V _{OL}	Output Voltage Low ¹		-150		150	mV
V _{OMAX}	Output Voltage Maximum ¹	Measurement on single ended signal using absolute value		816	1150	mV
V _{OMIN}	Output Voltage Minimum ¹		-300	-42		mV
V _{OSWING}	Output Swing Voltage ^{1,2,3}	Scope averaging off	300	1634		mV
V _{OC}	Output Cross Voltage ^{1,2,4}		250	430	550	mV
DV _{OC}	VOC Magnitude Change ^{1,2,5}			12	140	mV

Note:

1. At default SMBUS amplitude settings
2. Guaranteed by design and characterization, not 100% tested in production
3. Measured from differential waveform
4. This one is defined as voltage where Q+ = Q- measured on a component test board and only applied to the differential rising edge
5. The total variation of all Vcross measurements in any particular system. This is a subset of Vcross_min/max allowed.

HCSL Output AC Characteristics

Temperature = T_A; Supply voltages per normal operation conditions; See test circuits for the load conditions

Symbol	Parameters	Condition	Min.	Typ.	Max.	Units
f _{OUT}	Output Frequency			100		MHz
t _{RF}	Slewrate ^{1,2,3}	Scope averaging on fast setting	2	2.3	4	V/ns
		Scope averaging on slow setting	1.1	1.9	2.9	V/ns
D _{tRF}	Slewrate matching ^{1,2,4}	Scope averaging on		3		%
t _{DC}	Duty Cycle ^{1,2}	Measured differentially, PLL Mode	45	50	55	%
t _{SKEW}	Output Skew ^{1,2}	Averaging on, V _T = 50%		43	60	ps
t _{jc-c}	Cycle to cycle jitter ^{1,2}			42	50	ps
t _{STARTUP}	Start up time				10	ms
t _{LOCK}	PLL lock time				20	ms



Symbol	Parameters	Condition	Min.	Typ.	Max.	Units
tjPHASE	Integrated phase jitter (RMS) 1,5,6	PCIe Gen1 (2.5 GT/s)	15	35	86	ps
		PCIe Gen2 Hi Band (5.0 GT/s)	0.4	0.6	3.0	ps
		PCIe Gen2 Lo Band (5.0 GT/s)	0.2	0.3	3.1	ps
		PCIe Gen3 (8.0 GT/s)	0.15	0.2	1.0	ps
		PCIe Gen4 (16.0 GT/s)	0.15	0.2	0.4	ps
		PCIe Gen5 (32.0 GT/s)	0.06	0.08	0.15	ps
		PCIe Gen6 (64.0 GT/s)	0.03	0.05	0.1	ps

Note:

1. Guaranteed by design and characterization, not 100% tested in production
2. Measured from differential waveform
3. Slew rate is measured through the Vswing voltage range centered around differential 0V, within +/-150mV window
4. It is measured using a +/-75mV window centered on the average cross point
5. See <http://www.pcisig.com> for complete specs
6. Sample size of at least 100k cycles. This can be extrapolated to 108ps pk-pk @ 1M cycles for a BER of 10⁻¹²

Differential Output Clock Periods - Spread Spectrum Disabled ^{1, 2}

Center Freq. MHz	Measurement Window							Units
	1 clock	1 us	0.1 s	0.1 s	0.1 s	1 us	1 clock	
	-c2cjitter AbsPer Min	-SSC Short-term Avg. Min	-ppmLong- term Avg. min	0 ppm Period Nominal	+ppm Long- term Avg. max	+SSC Short-term Avg. Max	-c2cjitter AbsPer Max	
100.00	9.94900		9.99900	10.00000	10.00100		10.05100	ns

Differential Output Clock Periods - Spread Spectrum Enabled ^{1, 2}

Center Freq. MHz	Measurement Window							Units
	1 clock	1 us	0.1 s	0.1 s	0.1 s	1 us	1 clock	
	-c2cjitter AbsPer Min	-SSC Short-term Avg. Min	-ppmLong- term Avg. min	0 ppm Period Nominal	+ppm Long- term Avg. max	+SSC Short-term Avg. Max	-c2cjitter AbsPer Max	
99.75	9.94906	9.99906	10.02406	10.02506	10.02607	10.05107	10.10107	ns

Note:

1. Guaranteed by design and characterization, not 100% tested in production
2. All long term accuracy and clock period specifications are guaranteed assuming REF is trimmed to 50.00MHz



SMBus Interface Information

Write Operation

- Controller (host) sends a start bit
- Controller (host) sends the write address
- RSM clock will acknowledge
- Controller (host) sends the beginning byte location = N
- RSM clock will acknowledge
- Controller (host) sends the byte count = X
- RSM clock will acknowledge
- Controller (host) starts sending Byte N through Byte N+X-1
- RSM clock will acknowledge each byte one at a time
- Controller (host) sends a stop bit

Write Operation			
Controller (Host)			RSM (Slave/Receiver)
T	start bit		
Slave Address			
WR	Write		
			ACK
Beginning Byte = N			
			ACK
Data Byte Count = X			
			ACK
Beginning Byte N			
			ACK
O		X Byte	
O			O
O			O
			O
Byte N + X - 1			
			ACK
P	stop bit		

Read Operation

- Controller (host) will send a start bit
- Controller (host) sends the write address
- RSM clock will acknowledge
- Controller (host) sends the beginning byte location = N
- RSM clock will acknowledge
- Controller (host) will send a separate start bit
- Controller (host) sends the read address
- RSM clock will acknowledge
- RSM clock will send the data byte count = X
- RSM clock sends Byte N+X-1
- RSM clock sends Byte 0 through Byte X (if X(H) was written to Byte 8)
- Controller (host) will need to acknowledge each byte
- Controller (host) will send a not acknowledge bit
- Controller (host) will send a stop bit

Read Operation			
Controller (Host)			RSM (Slave/Receiver)
T	start bit		
Slave Address			
WR	Write		
			ACK
Beginning Byte = N			
			ACK
RT	Repeat start		
Slave Address			
RD	Read		
			ACK
			Data Byte Count=X
ACK			
		X Byte	Beginning Byte N
ACK			
			O
O			O
O			O
O			
			Byte N + X - 1
N	Not acknowledge		
P	stop bit		



SMBus Address Assignment

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	0	SADR	0	1/0

Note: SMBus address is latched on SADR pin

Byte 0: Output Enable Register ¹

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	Q7_OE	Q7 output enable	RW	1	Low/Low	Enabled
6	Q6_OE	Q6 output enable	RW	1	Low/Low	Enabled
5	Q5_OE	Q5 output enable	RW	1	Low/Low	Enabled
4	Q4_OE	Q4 output enable	RW	1	Low/Low	Enabled
3	Q3_OE	Q3 output enable	RW	1	Low/Low	Enabled
2	Q2_OE	Q2 output enable	RW	1	Low/Low	Enabled
1	Q1_OE	Q1 output enable	RW	1	Low/Low	Enabled
0	Q0_OE	Q0 output enable	RW	1	Low/Low	Enabled

Note:

1. A low on these bits will override the OE# pins and force the differential outputs to Low/Low states

Byte 1: SS Readback and Control Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	SSEN RB1	SS Enable Readback Bit1	R	Latch	'00' for SS_SEL_TRI = '0', '01' for SS_SEL_TRI = 'M', '11' for SS_SEL_TRI = '1'	
6	SSEN RB0	SS Enable Readback Bit0	R	Latch		
5	SSEN_SWCTR	Enable SW control of SS	RW	0	Values in B1[7:6] control SS amount	Values in B1[4:3] control SS amount
4	SSEN SW1	SS enable SW control Bit1	RW ¹	0	'00' = SS off, '01' = -0.25% SS, '10' = Reserved, '11' = -0.5% SS	
3	SSEN SW0	SS enable SW control Bit0	RW ¹	0		
2	Reserved			1		
1	Amplitude1	Control output amplitude	RW	1	'00' = 0.6V, '01' = 0.7V, '10' = 0.8V, '11' = 0.9V	
0	Amplitude0		RW	0		

Note:

1. B1[5] must be set to a 1 for these bits to have any effect on the part.



Byte 2: Differential Output Slew Rate Control Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	SLEWRATECTR_Q7	Control slew rate of Q7	RW	1	Slow setting	Fast setting
6	SLEWRATECTR_Q6	Control slew rate of Q6	RW	1	Slow setting	Fast setting
5	SLEWRATECTR_Q5	Control slew rate of Q5	RW	1	Slow setting	Fast setting
4	SLEWRATECTR_Q4	Control slew rate of Q4	RW	1	Slow setting	Fast setting
3	SLEWRATECTR_Q3	Control slew rate of Q3	RW	1	Slow setting	Fast setting
2	SLEWRATECTR_Q2	Control slew rate of Q2	RW	1	Slow setting	Fast setting
1	SLEWRATECTR_Q1	Control slew rate of Q1	RW	1	Slow setting	Fast setting
0	SLEWRATECTR_Q0	Control slew rate of Q0	RW	1	Slow setting	Fast setting

Byte 3: REF Control Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	REFSLEWRATE	Slew rate control for REF	RW	0	'00' = 0.9V/ns '01' = 1.3V/ns, '10' = 1.6V/ns, '11' = 1.8V/ns	
6			RW	1		
5	REF_PDSTATE	Wake-on-Lan enable for REF	RW	0	REF = 'Low'	REF = running
4	REF_OE	Output enable for REF	RW	1	REF = "Low"	REF = running
3	Reserved			1		
2	Reserved			1		
1	Reserved			1		
0	Reserved			1		

Byte 4: Reserved

Bit	Control Function	Description	Type	Power Up Condition	0	1
7:0	Reserved					



Byte 5: Revision and Vendor ID Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	RID3	Revision ID	R	0	Rev = 0000	
6	RID2		R	0		
5	RID1		R	0		
4	RID0		R	0		
3	PVID3	Vendor ID	R	0	RSM=0001	
2	PVID3		R	0		
1	PVID3		R	0		
0	PVID3		R	1		

Byte 6: Device Type/Device ID Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	DTYPE1	Device type	R	0	'00' = CG, '01' = ZDB, '10' = Reserve, '11' = ZDB	
6	DTYPE0		R	0		
5	DID5	Device ID	R	0	001000 binary, 08Hex	
4	DID4		R	0		
3	DID3		R	1		
2	DID2		R	0		
1	DID1		R	0		
0	DID0		R	0		

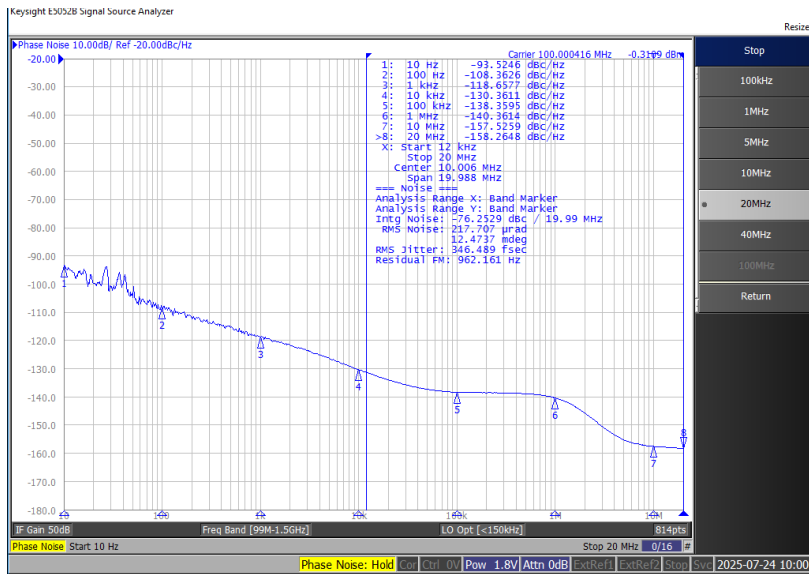
Byte 7: Byte Count Register

Bit	Control Function	Description	Type	Power Up Condition	0	1
7	Reserved			0		
6	Reserved			0		
5	Reserved			0		
4	BC4	Byte count programming	RW	0	Writing to this register will configure how many bytes will be read back, default is 8 bytes	
3	BC3		RW	1		
2	BC2		RW	0		
1	BC1		RW	0		
0	BC0		RW	0		

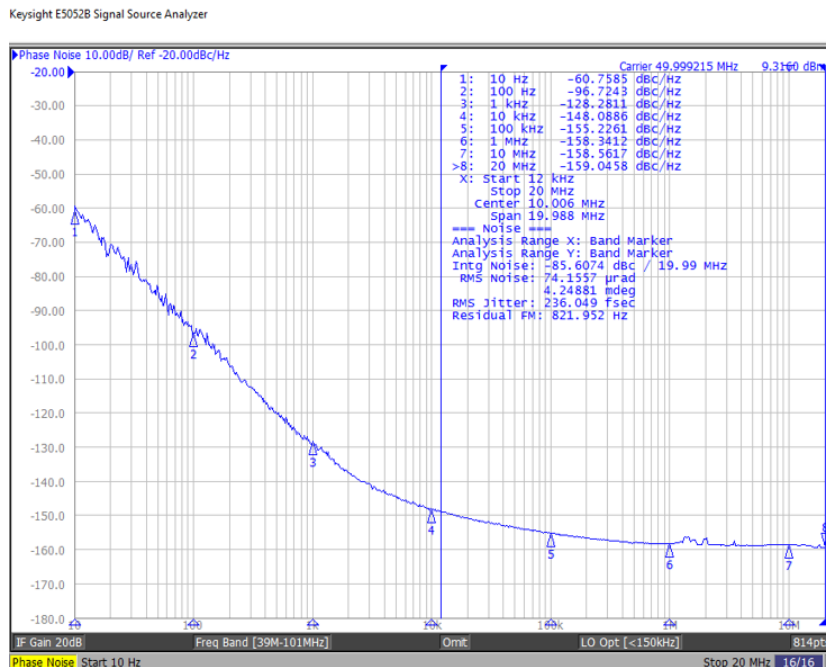


Phase Jitter Parameter

100MHz HCSL Clock (12k to 20MHz)



50MHz CMOS Clock



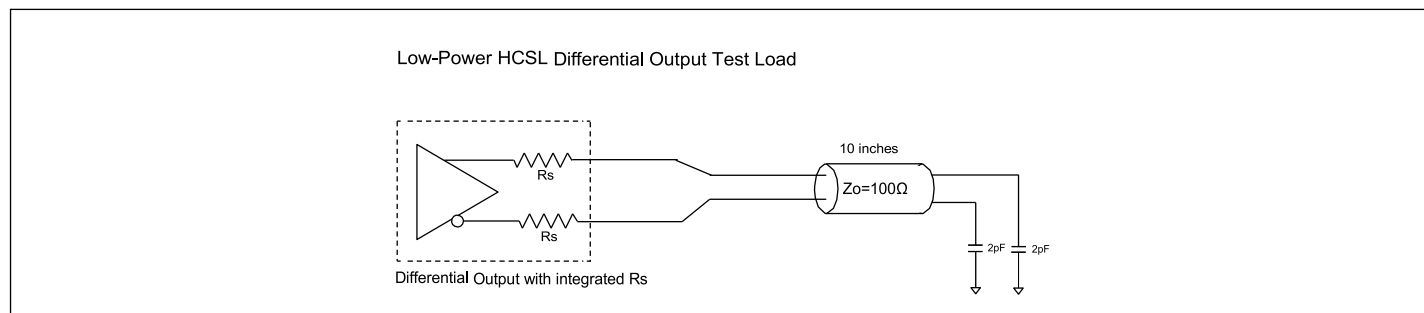


Figure 1. Low Power HCSL Test Circuit

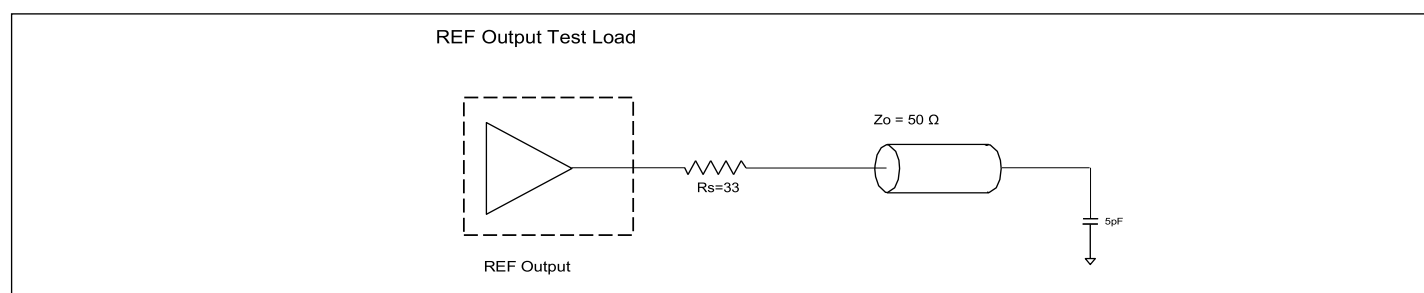


Figure 2. CMOS REF Test Circuit

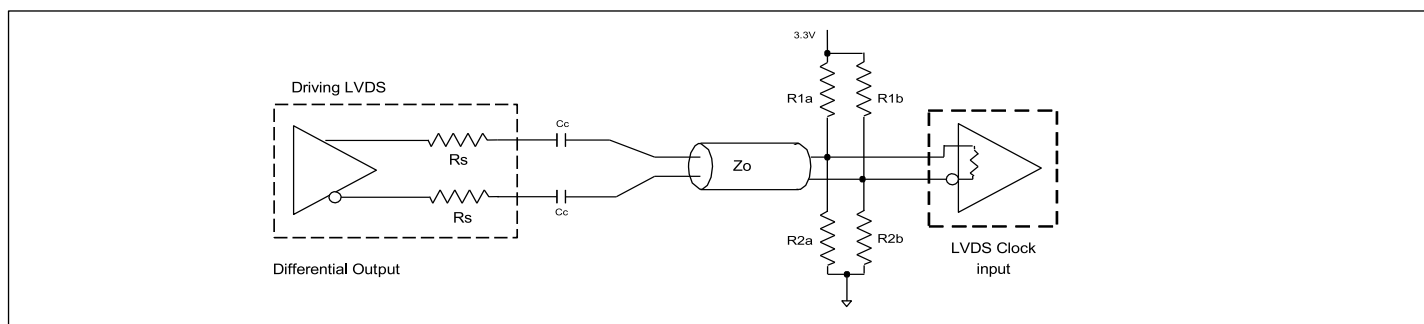


Figure 3. Differential Output driving LVDS

Alternate Differential Output Terminations

Component	Receiverwithtermination	Receiverwithouttermination	Unit
R_{1a}, R_{1b}	10,000	140	Ω
R_{2a}, R_{2b}	5,600	75	Ω
CC	0.1	0.1	μF
VCM	1.2	1.2	V

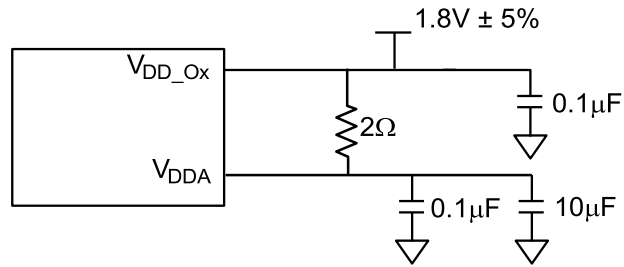


Figure 4. Power Supply Filter

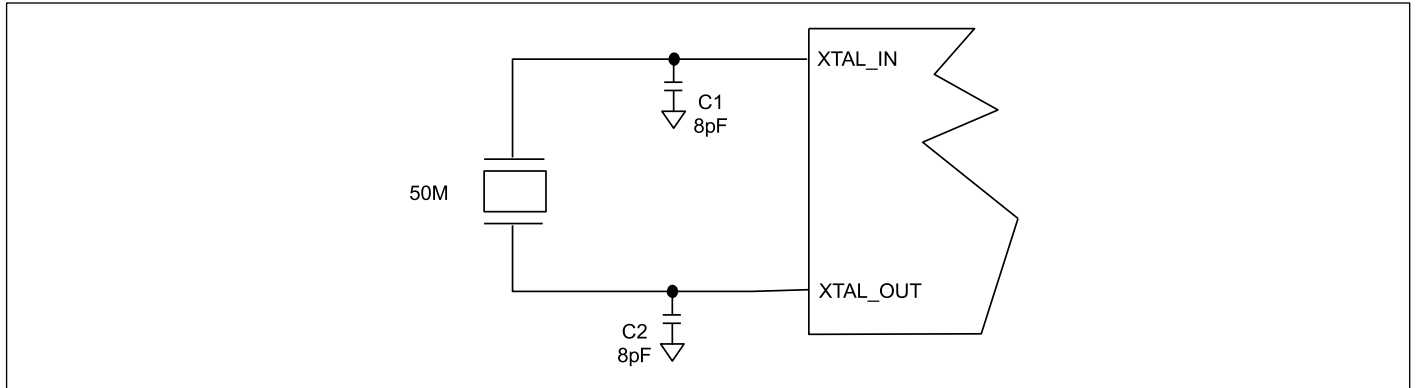


Applications

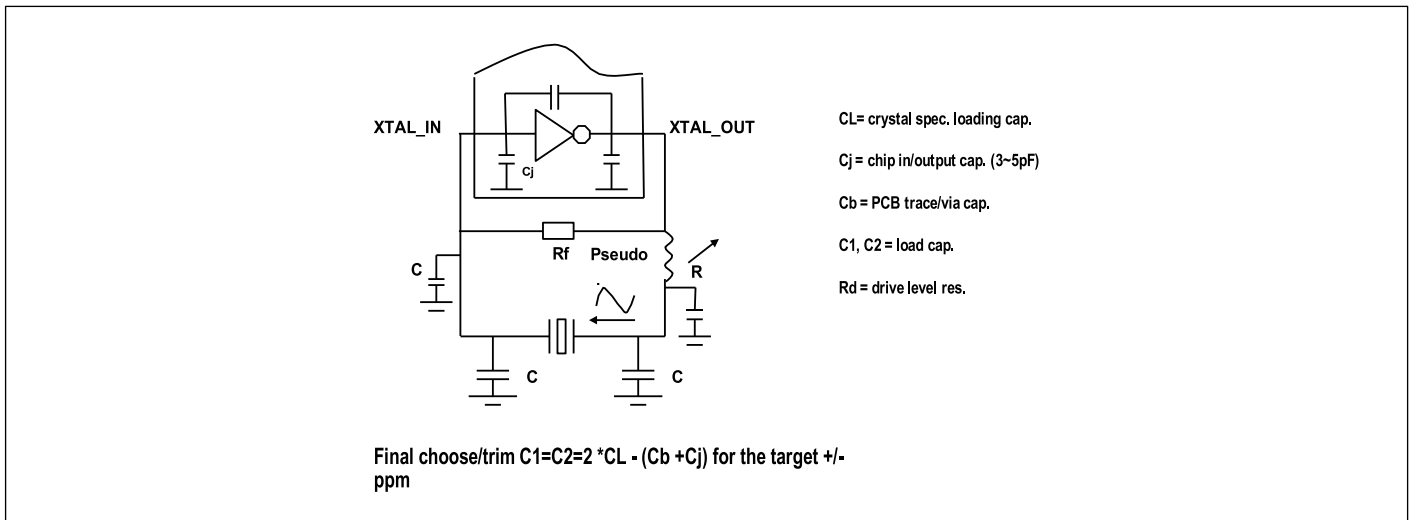
Crystal circuit connection

The following diagram shows RS2CG1818 crystal circuit connection with a parallel crystal. For the CL=8pF crystal, it is suggested to use C1=8pF, C2=8pF. C1 and C2 can be adjusted to fine tune to the target ppm of crystal oscillator according to different board layouts based on the following formular in the Crystal Capacitor Calculation diagram.

Crystal Oscillator Circuit



Crystal Capacitor Calculation



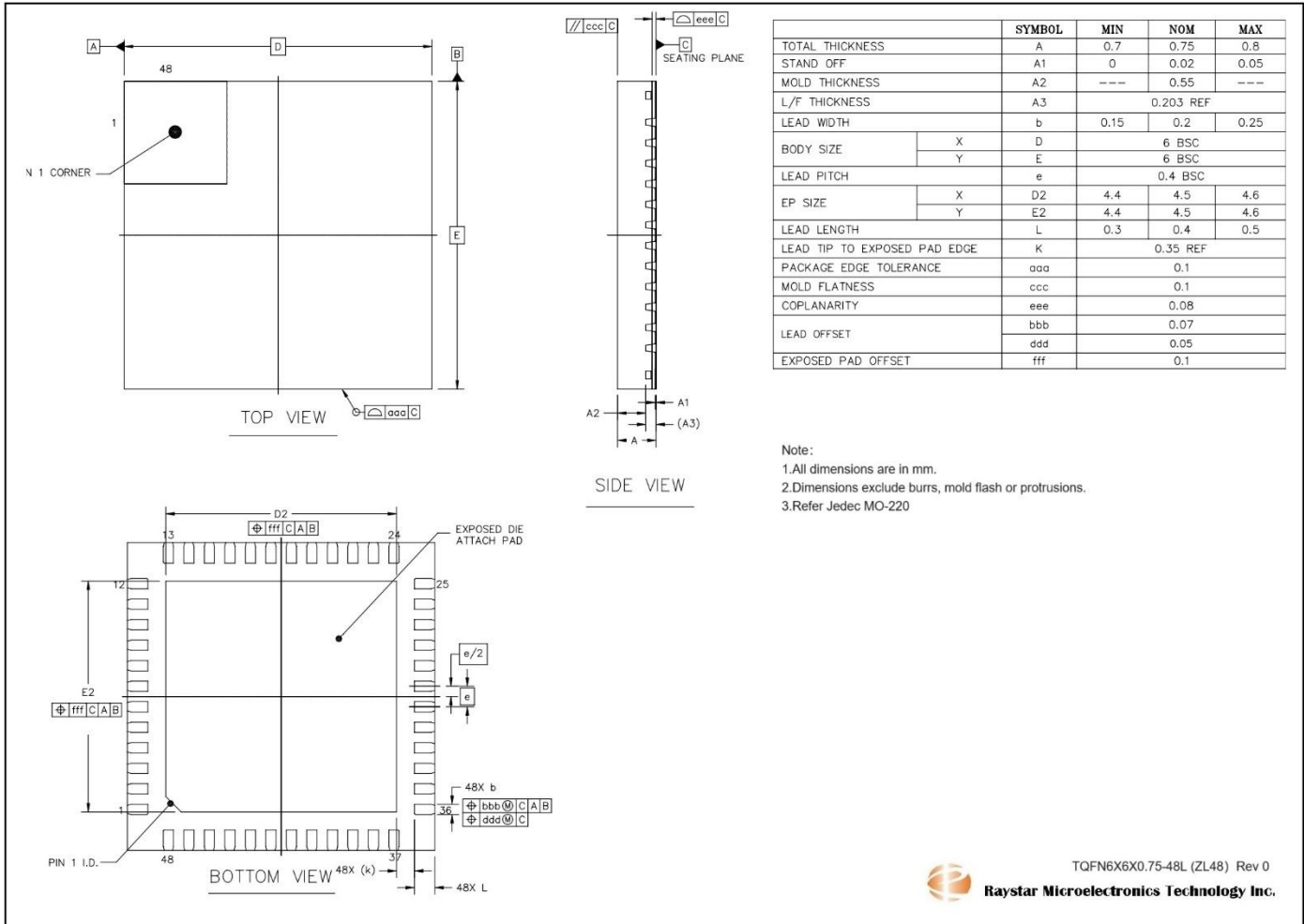
Recommended Crystal Specification

- a) 50MHz, CL=8pF, +/-20ppm



Package Information

TQFN-48L





Revision History

Revision	Description	Date
1.0	Initial release	2025/11/19